

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
20V	380m $\Omega$ @4.5V	0.75A
	450m $\Omega$ @2.5V	
	800m $\Omega$ @1.8V	

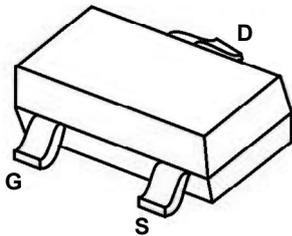
### Feature

- High density cell design for ultra low on-resistance
- High-Side Switching
- Rugged and reliable
- ESD Protect

### Application

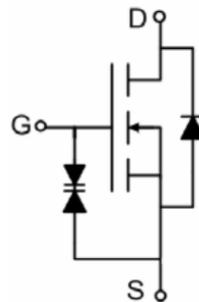
- Battery Management for Ultra Small Portable Electronics
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

### Package

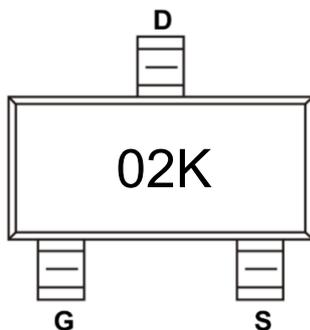


SOT-523

### Circuit diagram



### Marking



### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	V
Continuous Drain Current	$I_D$	0.75	A
Pulsed Drain Current	$I_{DM}$	1.8	A
Power Dissipation	$P_D$	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 ~ +150	°C

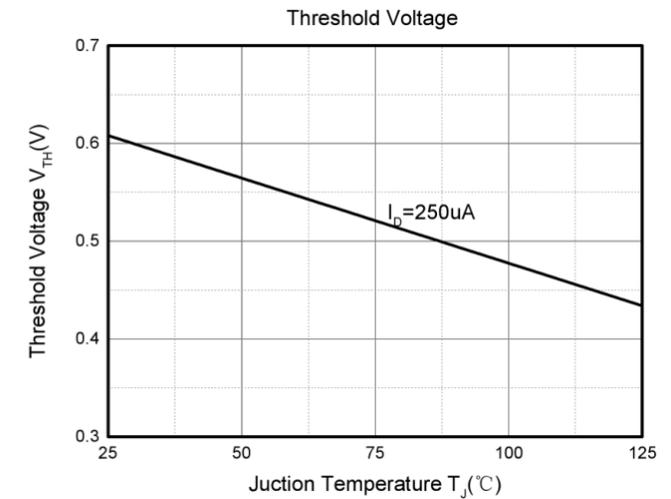
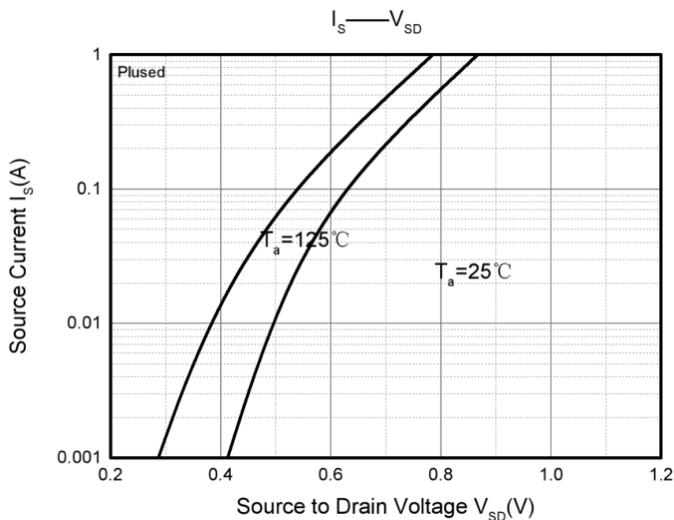
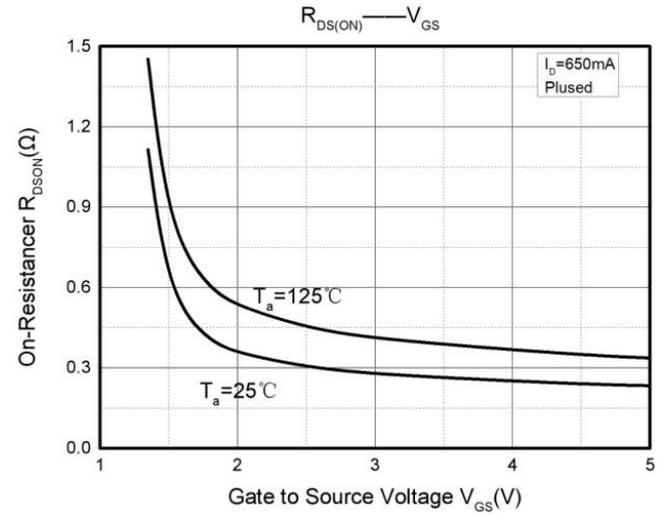
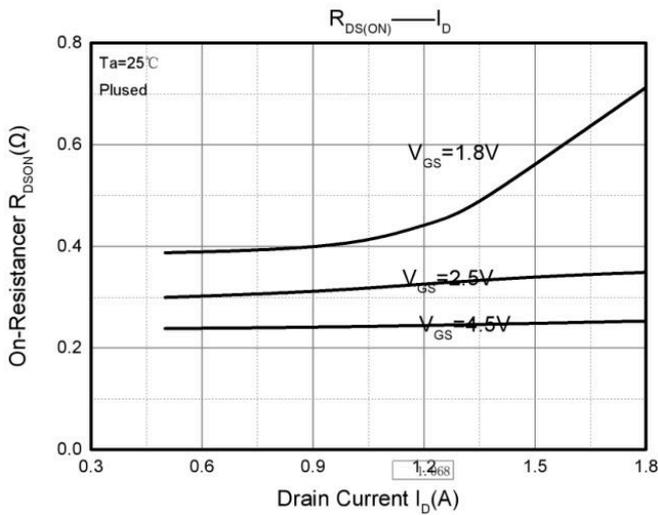
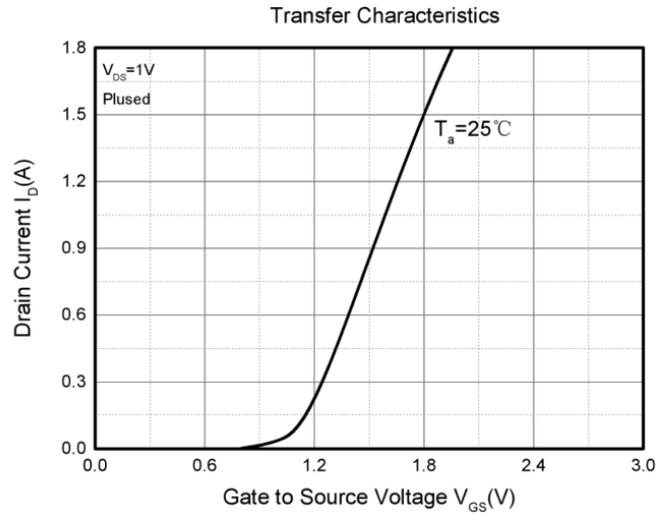
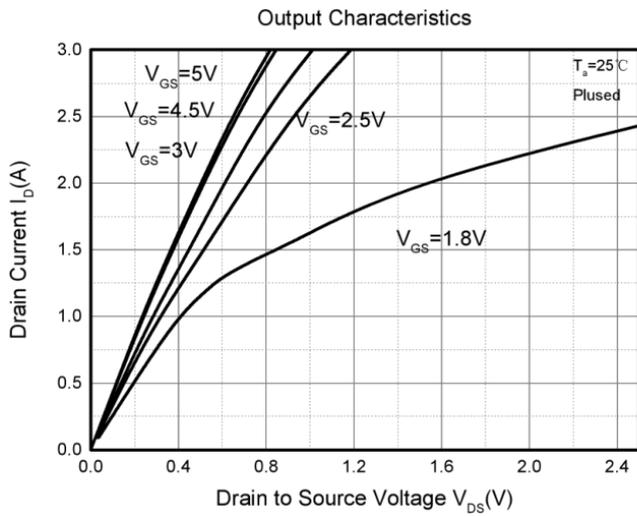
### Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.3	0.65	1	V
Drain-source on-resistance <sup>1)</sup>	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 0.5A$		250	380	mΩ
		$V_{GS} = 2.5V, I_D = 0.5A$		350	450	
		$V_{GS} = 1.8V, I_D = 0.5A$		400	800	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79		pF
Output Capacitance	$C_{oss}$			13		
Reverse Transfer Capacitance	$C_{rss}$			9		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4.5V, I_D = 0.5A, R_{GEN} = 10\Omega$		6.7		nS
Turn-on rise time	$t_r$			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	$t_f$			7.4		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$V_{DS}$	$V_{GS} = 0V, I_S = 0.5A$			1.3	V

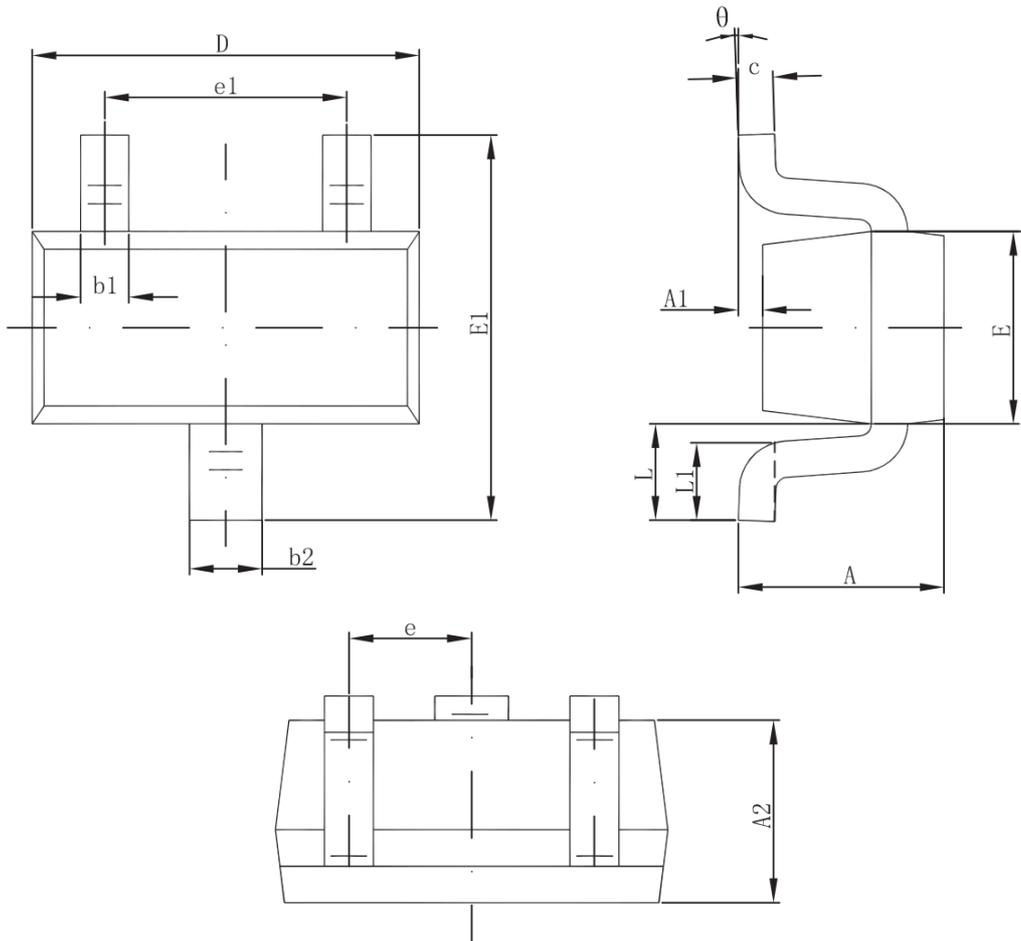
Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics



### SOT-523 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
B2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°